

ABSTRACT

A method for detecting endpoint of plasma-assisted etch process by monitoring a parameter of the etch process, such as an automatic matching network parameter, and detecting a predetermined change in the parameter signaling the endpoint. This novel endpoint detection method has advantages of, *inter alia*, simplicity and reliability, is very cost-effective and requires minimum change to the etch process system hardware. It is particularly useful in the manufacture of photomasks and products manufactured using photomasks.